

Abstract of the Disclosure

In a magnetic random access memory (MRAM) having a transistor and a magnetic tunneling junction (MTJ) layer in a unit cell, the MTJ layer includes a lower magnetic layer, an oxidation preventing layer, a tunneling oxide layer, and an upper magnetic layer, which are sequentially stacked. The tunneling oxide layer may be formed using an atomic layer deposition (ALD) method. At least the oxidation preventing layer may be formed using a method other than the ALD method.